



TGD N&P-Channel complementary Power MOSFET

**Description**

The TGD30D2519K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

**General Features**

**N channel**

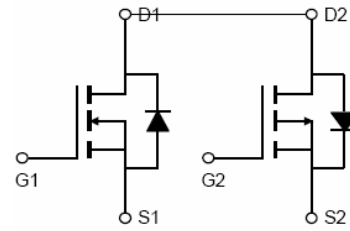
- $V_{DS} = 30V, I_D = 25A$
- $R_{DS(ON)} < 12m\Omega @ V_{GS} = 10V$
- $R_{DS(ON)} < 18m\Omega @ V_{GS} = 4.5V$

**p channel**

- $V_{DS} = -30V, I_D = -19A$
- $R_{DS(ON)} < 35m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} < 65m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

**Application**

- H-bridge
- Inverters



Schematic diagram



**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
30D2519K	30D2519K	TO-252-4L	-	-	-

**Absolute Maximum Ratings ( $T_C = 25^\circ C$  unless otherwise noted)**

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	$V_{DS}$	30	-30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V	
Continuous Drain Current	$I_D$	$T_C = 25^\circ C$	25	-19	A
		$T_C = 100^\circ C$	17.7	-13.4	
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	90	-60	A	
Maximum Power Dissipation	$P_D$	21		W	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175		$^\circ C$	

**Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	7	$^\circ C/W$
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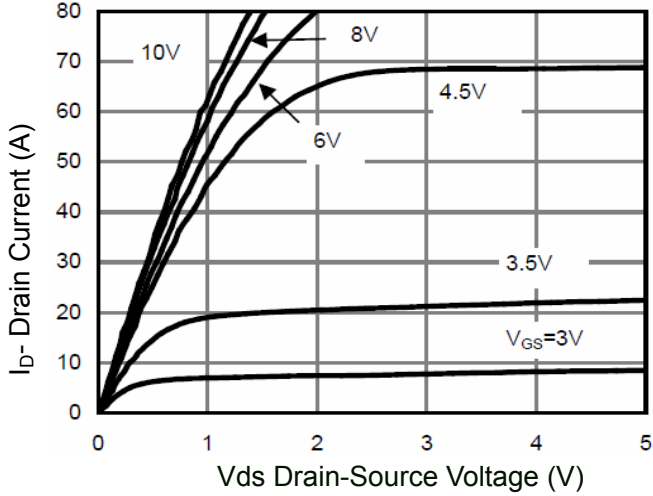
**N-Channel Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	2.0	3.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =7A	-	8.5	12	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	11.8	18	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =7A	-	29	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	450	-	PF
Output Capacitance	C <sub>oss</sub>		-	150	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	90	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =2.5Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	12	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	19	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	6	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =6A, V <sub>GS</sub> =10V	-	9.5		nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.0		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1.9		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =25A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	25	A

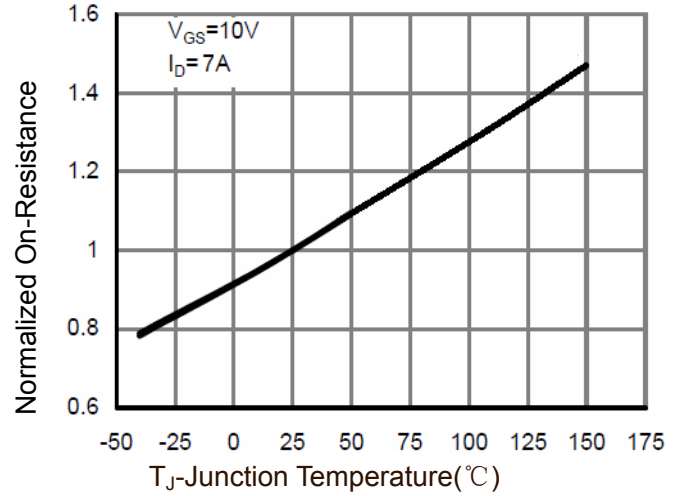
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω

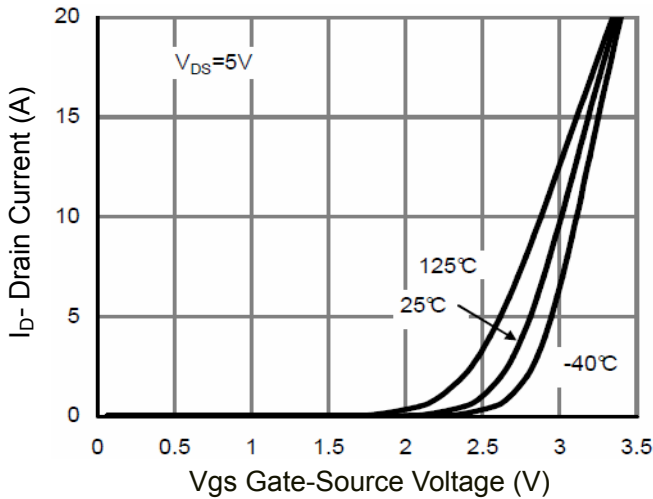
**N-Channel Typical Electrical and Thermal Characteristics (Curves)**



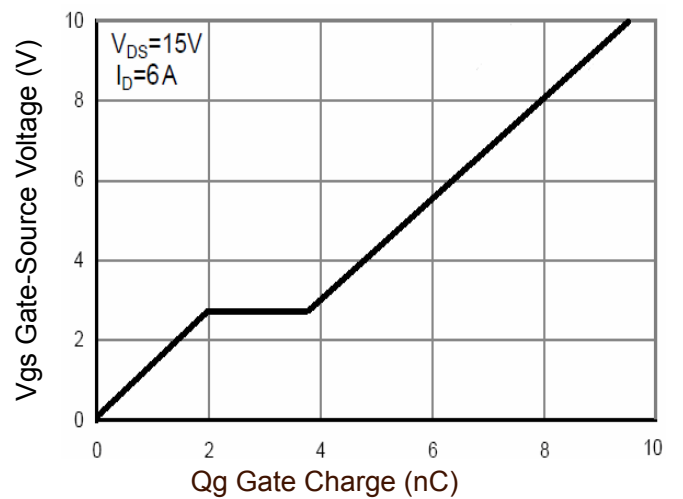
**Figure 1 Output Characteristics**



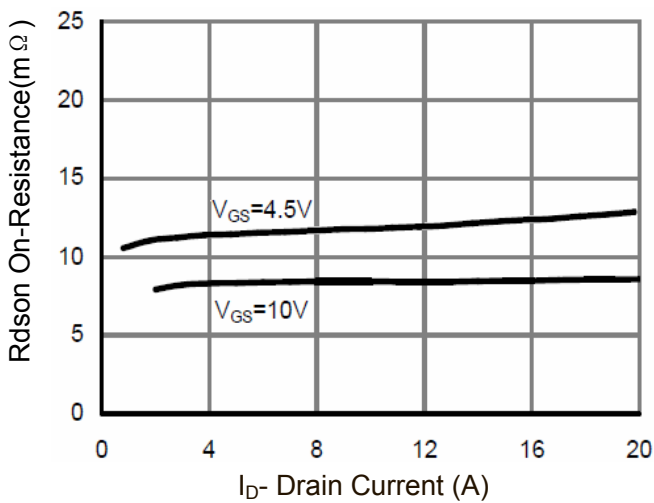
**Figure 4 Rdson-Junction Temperature**



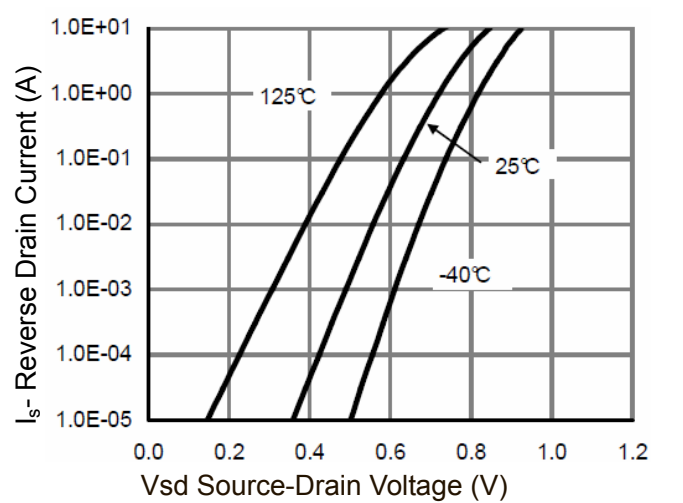
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rdson- Drain Current**



**Figure 6 Source- Drain Diode Forward**

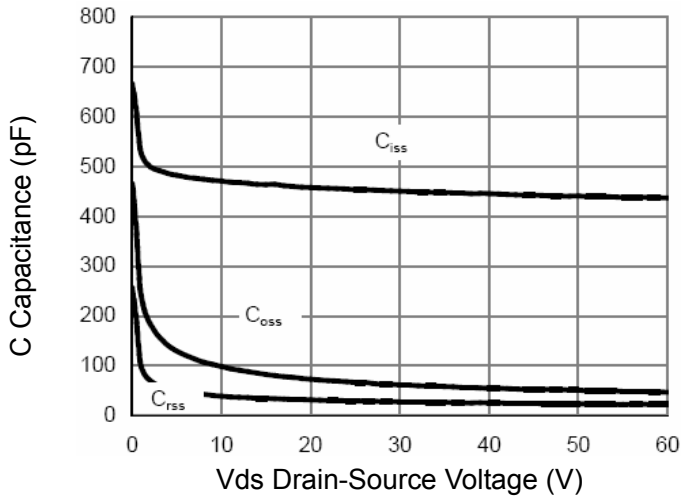


Figure 7 Capacitance vs Vds

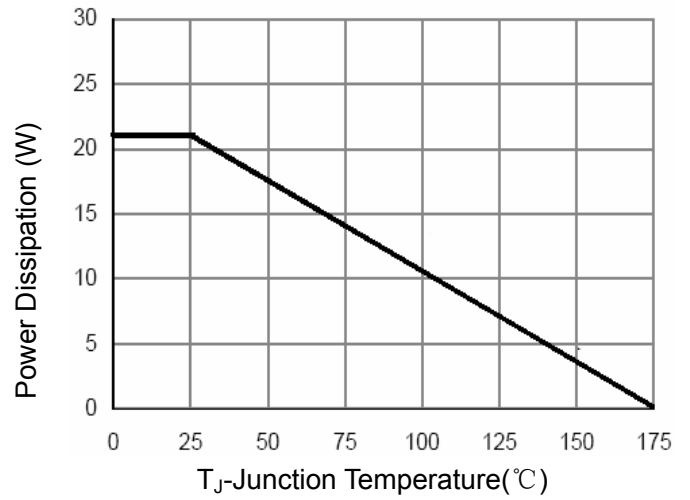


Figure 9 Power De-rating

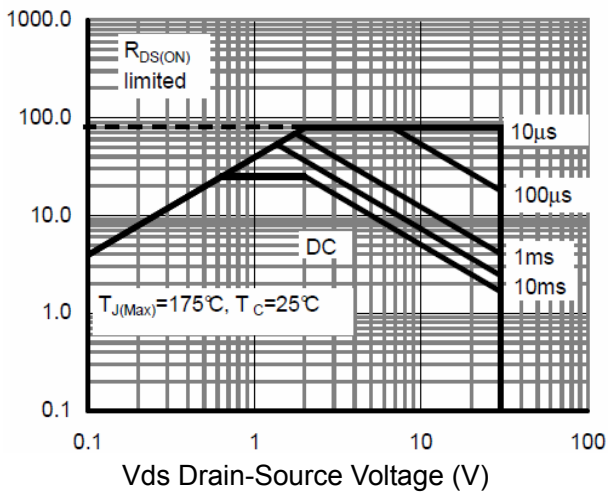


Figure 8 Safe Operation Area

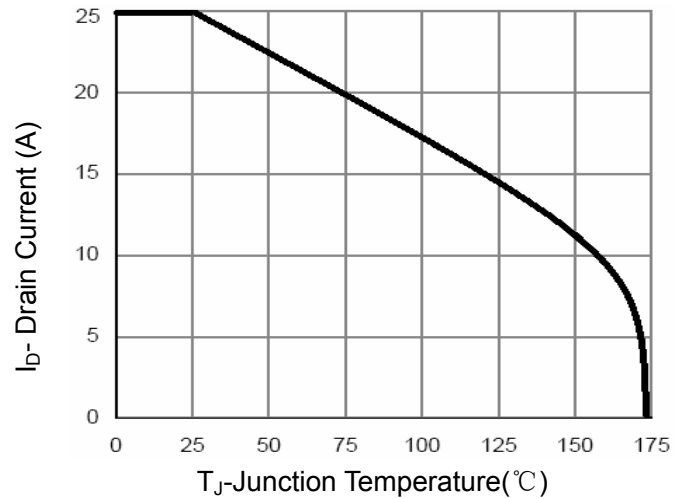


Figure 10 Current De-rating

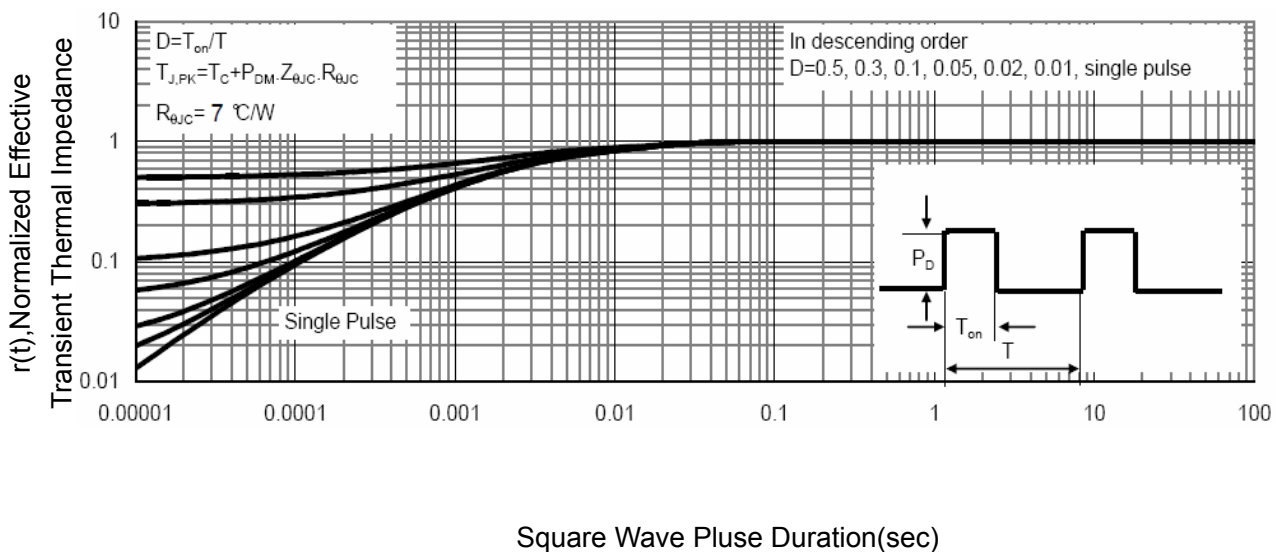


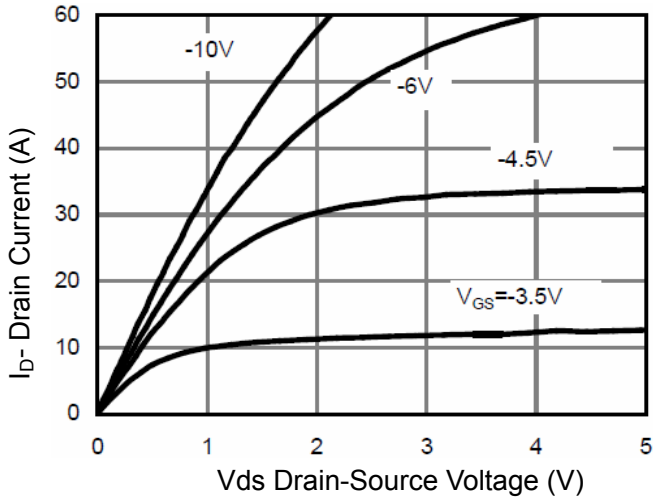
Figure 11 Normalized Maximum Transient Thermal Impedance



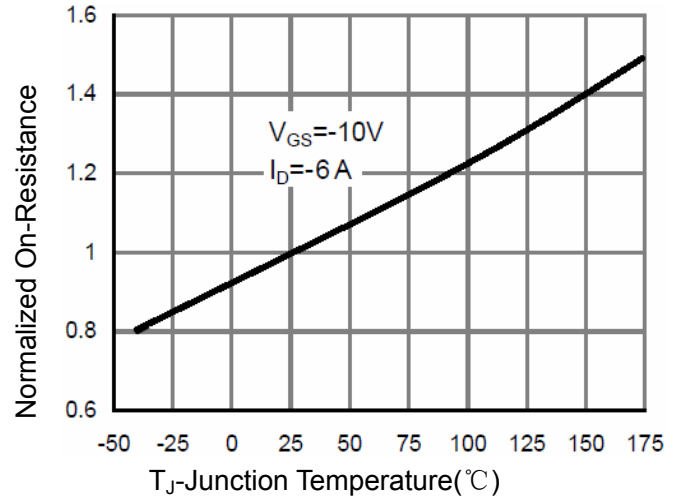
**P-Channel Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.8	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6A	-	28	35	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	-	48	65	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6A	-	15	-	S
<b>Dynamic Characteristics</b> (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, F=1.0MHz	-	920	-	PF
Output Capacitance	C <sub>oss</sub>		-	140	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	90	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, R <sub>L</sub> =2.5Ω V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω	-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	30	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	22	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	26	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-6A, V <sub>GS</sub> =-10V	-	16.2	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.9	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-6A	-	-	-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-19	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = -6A di/dt = 100A/μs (Note3)	-	23	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	14	-	nC

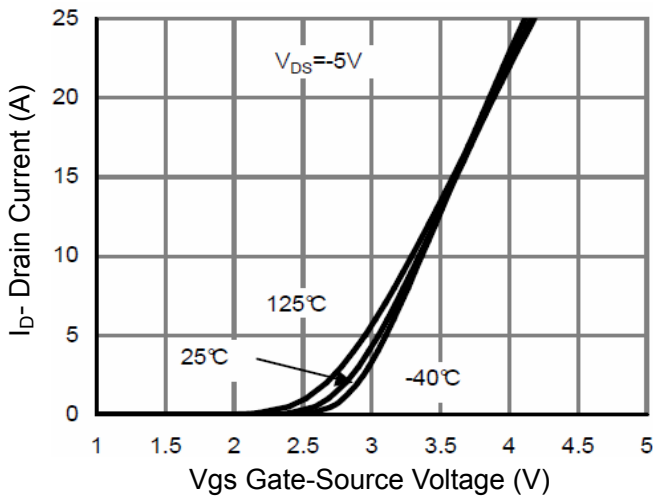
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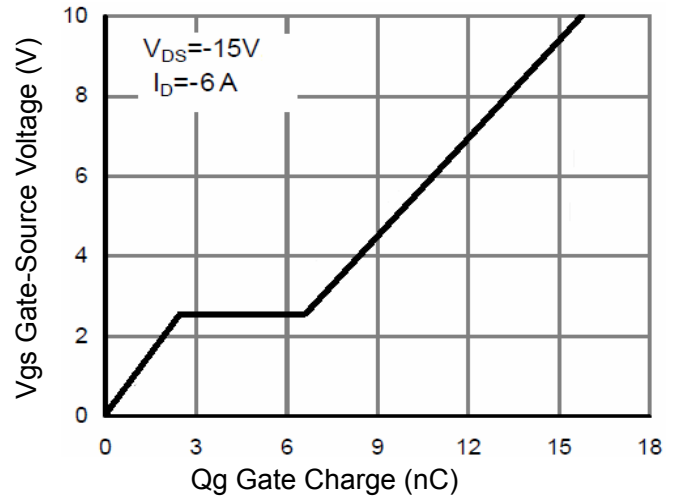
**Figure 1 Output Characteristics**



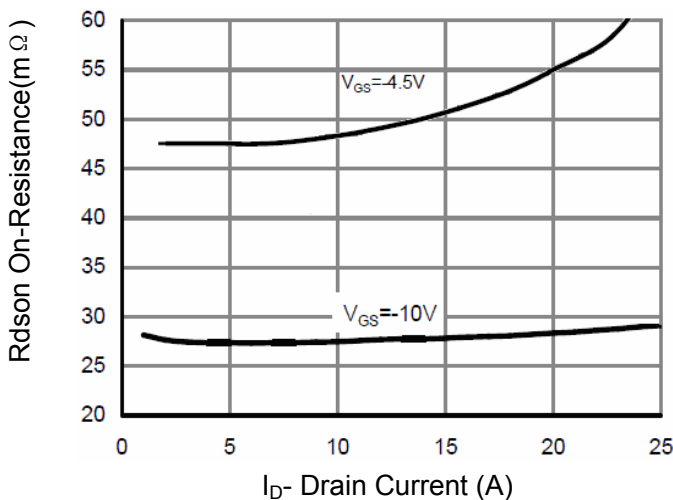
**Figure 4 Rdson-Junction Temperature**



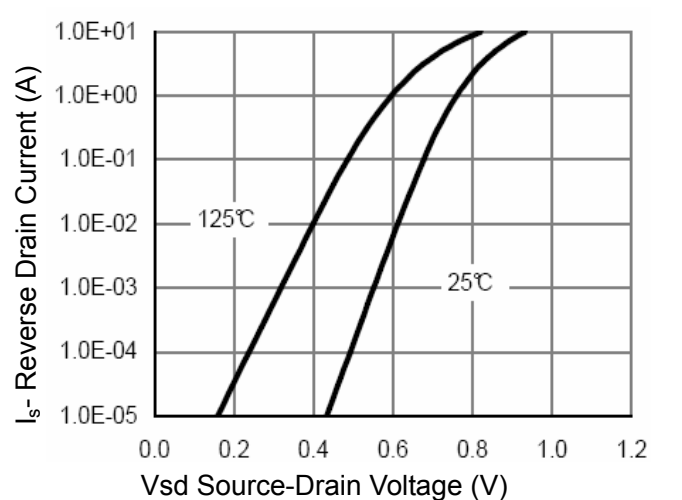
**Figure 2 Transfer Characteristics**



**Figure 5 Gate Charge**



**Figure 3 Rdson- Drain Current**



**Figure 6 Source- Drain Diode Forward**

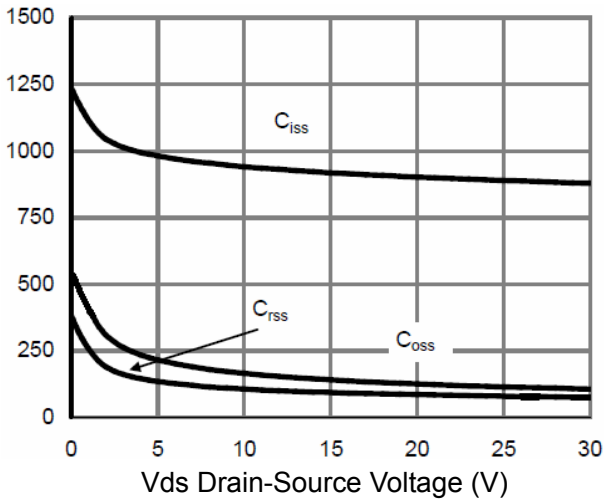


Figure 7 Capacitance vs Vds

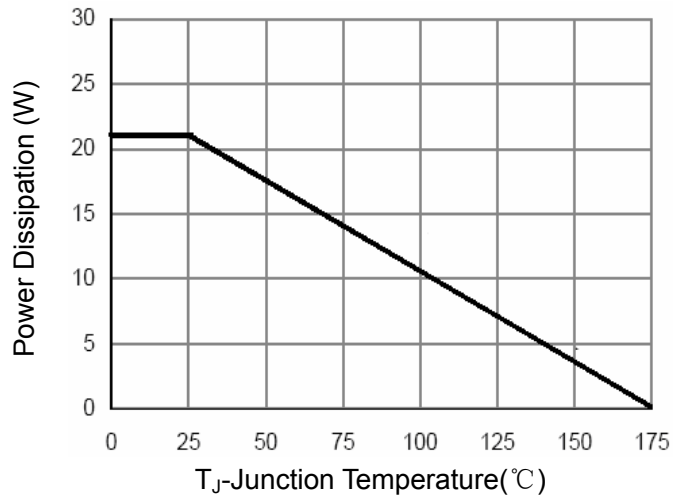


Figure 9 Power De-rating

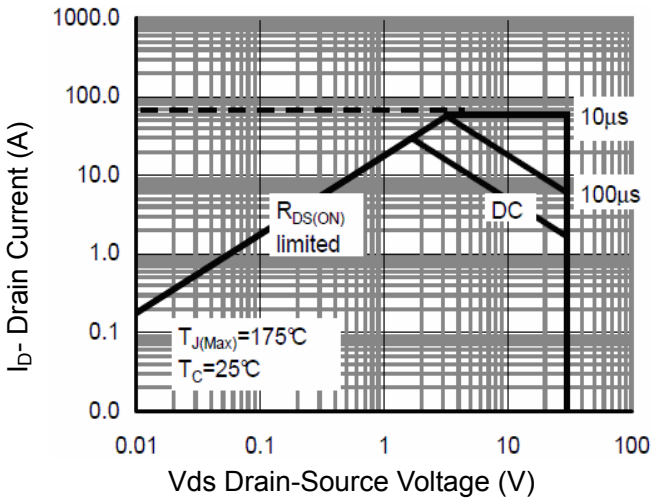


Figure 8 Safe Operation Area

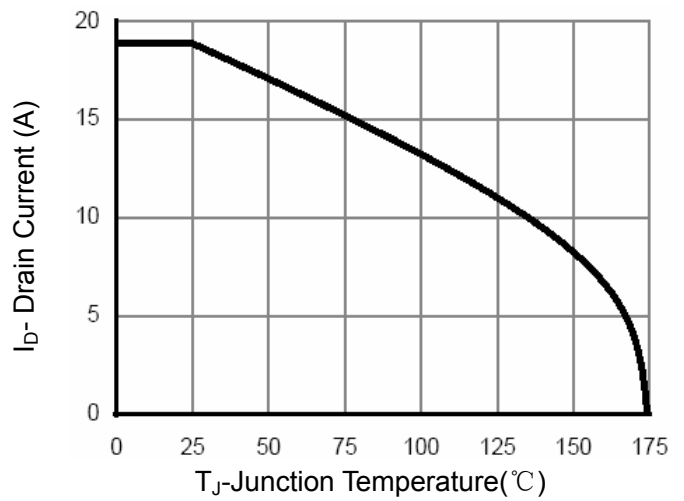


Figure 10 Current De-rating

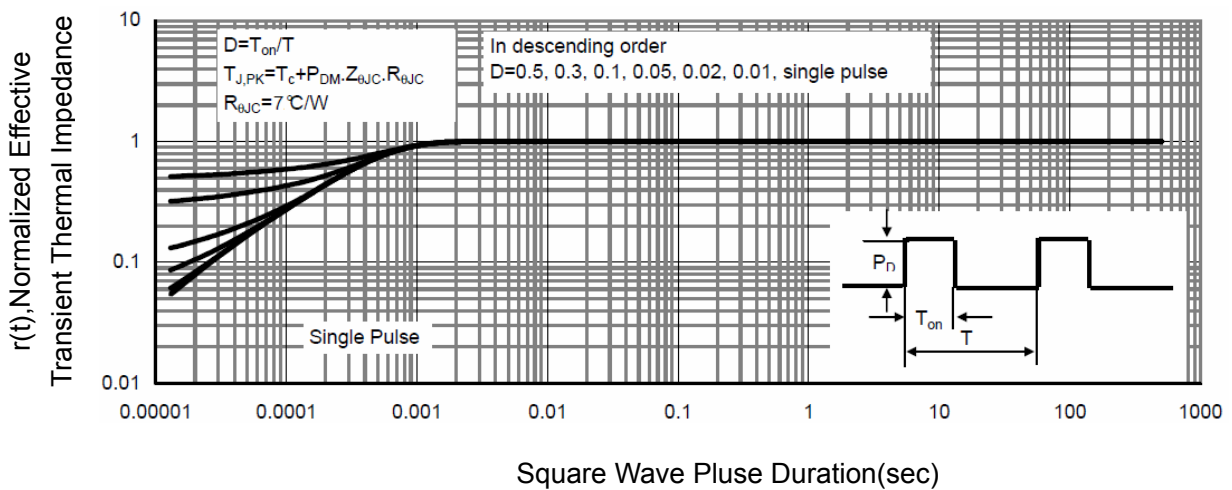
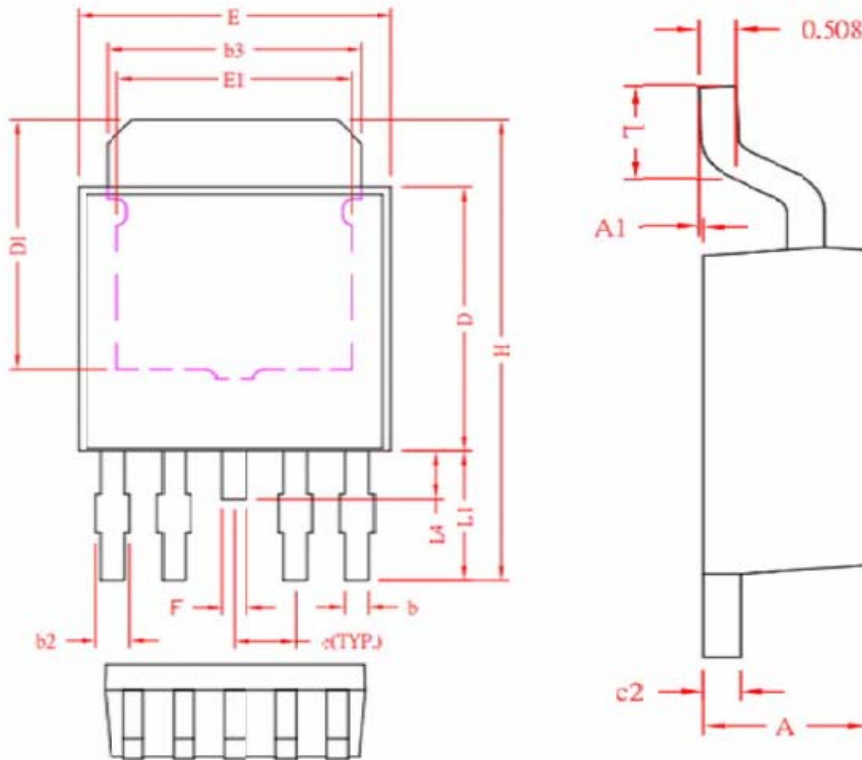


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-4L Package Information



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0	0.08	0.15
b	0.45	0.53	0.60
b2	0.50	0.65	0.80
b3	5.20	5.35	5.50
c2	0.45	0.50	0.55
D	5.40	5.60	5.80
D1	4.57	-	-
E	6.40	6.60	6.80
E1	3.81	-	-
e	1.27 REF.		
F	0.40	0.50	0.60
H	9.40	9.80	10.20
L	1.40	1.59	1.77
L1	2.40	2.70	3.00
L4	0.80	1.00	1.20